

# N-Channel Shielded Gate PowerTrench<sup>®</sup> MOSFET 150 V, 2.3 A, 144 m $\Omega$

#### Features

- Shielded Gate MOSFET Technology
- Max  $r_{DS(on)}$  = 144 m $\Omega$  at  $V_{GS}$  = 10 V,  $I_D$  = 2.3 A
- Max  $r_{DS(on)}$  = 188 m $\Omega$  at  $V_{GS}$  = 6 V,  $I_D$  = 1.9 A
- High performance trench technology for extremely low r<sub>DS(on)</sub>
- High power and current handling capability in a widely used surface mount package

S

Pin 1

SuperSOT<sup>™</sup> -6

n

D

- Fast switching speed
- 100% UIL Tested
- RoHS Compliant

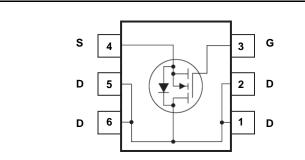


## **General Description**

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench<sup>®</sup> process that incorporates Shielded Gate technology. This process has been optimized for  $r_{DS(on)}$ , switching performance and ruggedness.

## Applications

- Load Switch
- Synchronous Rectifier
- Primary Switch



# MOSFET Maximum Ratings T<sub>A</sub> = 25 °C unless otherwise noted

Symbol	Parameter		Parameter Ratings		Ratings	Units
V <sub>DS</sub>	Drain to Source Voltage		150	V		
V <sub>GS</sub>	Gate to Source Voltage		±20	V		
-	Drain Current -Continuous	(Note 1a)	2.3	_		
D	-Pulsed		10	Α		
E <sub>AS</sub>	Single Pulse Avalanche Energy	(Note 3)	12	mJ		
P <sub>D</sub>	Power Dissipation	(Note 1a)	1.6			
	Power Dissipation	(Note 1b)	0.8			
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C		

#### **Thermal Characteristics**

$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	30	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient (Note 1	a) 78	0/10

#### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
.244	FDC86244	SSOT-6	7 "	8 mm	3000 units

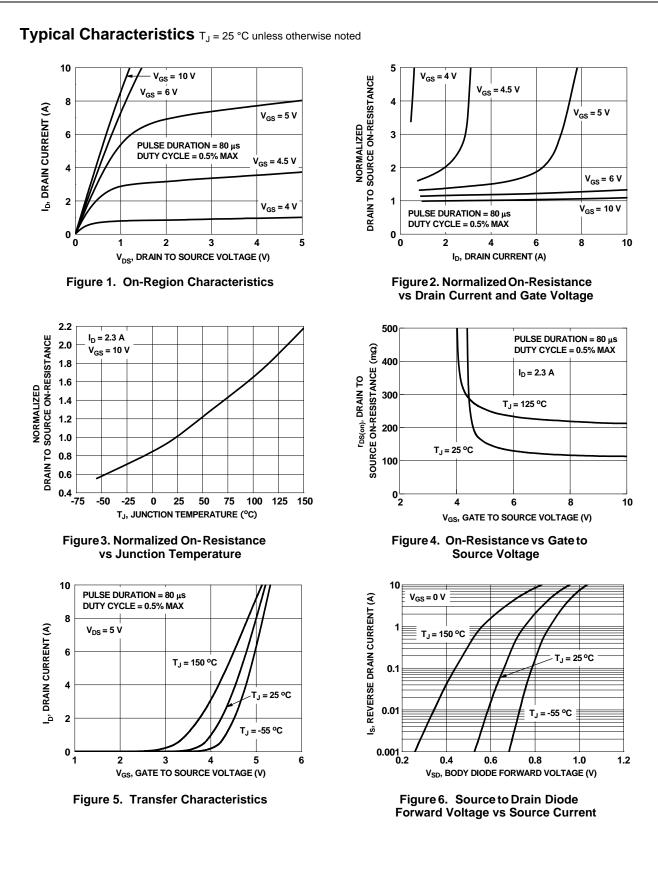
April 2015

$ \begin{array}{c} \Delta BV_{DSS} \\ \overline{\Delta T_J} \\ I_{DSS} \\ \overline{L_{SSS}} \\ $	istics in to Source Breakdown Voltage akdown Voltage Temperature officient o Gate Voltage Drain Current e to Source Leakage Current		nced to 25 °C	150	103		V mV/°C
$\begin{array}{c c} BV_{DSS} & Dra \\ \hline \Delta BV_{DSS} & Bre \\ \hline \Delta T_{J} & Coe \\ I_{DSS} & Zer \\ I_{GSS} & Gat \\ \end{array}$	in to Source Breakdown Voltage akdown Voltage Temperature efficient o Gate Voltage Drain Current	$I_{D} = 250 \ \mu A$ , reference $V_{DS} = 120 \ V$ , $V_{GS} = 120 \ V$ , $V_{SS} = 120 $	nced to 25 °C	150	103		
$\begin{array}{c} \Delta BV_{DSS} \\ \overline{\Delta T_J} \\ D_{DSS} \\ \overline{I_{OSS}} \\ \overline{I_{GSS}} \\ \end{array} \begin{array}{c} \overline{Gat} \\ \overline{On \ Character} \\ V_{GS(th)} \\ \end{array}$	efficient o Gate Voltage Drain Current	$I_{D} = 250 \ \mu A$ , reference $V_{DS} = 120 \ V$ , $V_{GS} = 120 \ V$ , $V_{SS} = 120 $	nced to 25 °C		103		mV/°C
I <sub>DSS</sub> Zer I <sub>GSS</sub> Gat <b>On Character</b> V <sub>GS(th)</sub> Gat	-		0.14				
<b>On Character</b> V <sub>GS(th)</sub> Gat	e to Source Leakage Current		V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V			1	μA
V <sub>GS(th)</sub> Gat		$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$				±100	nA
V <sub>GS(th)</sub> Gat	istics						
	e to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \ \mu A$		2.0	2.5	4.0	V
00(0)	e to Source Threshold Voltage	$I_D = 250 \ \mu$ A, referenced to 25 °C			-9		mV/°C
5	•	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.3 A			113	144	-
r <sub>DS(on)</sub> Stat	Static Drain to Source On Resistance	$V_{GS} = 6 \text{ V}, \text{ I}_{D} = 1.9 \text{ A}$			128	188	mΩ
- ( - )		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.			214	273	
g <sub>FS</sub> For	ward Transconductance	V <sub>DD</sub> = 5 V, I <sub>D</sub> = 2.3	A		6		S
Dynamic Cha	racteristics						
-	It Capacitance				260	345	pF
	put Capacitance	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 0 V, f = 1 MHz			32	45	pF
	erse Transfer Capacitance				1.7	5	pF
	e Resistance				1.3		Ω
Switching Ch	aracteristics						
t <sub>d(on)</sub> Tur	n-On Delay Time				4.7	10	ns
	e Time	V <sub>DD</sub> = 75 V, I <sub>D</sub> = 2.3			1.4	10	ns
t <sub>d(off)</sub> Tur	n-Off Delay Time	$V_{GS}$ = 10 V, $R_{GEN}$ = 6 $\Omega$			10	20	ns
1	Time				3.1	10	ns
	al Gate Charge	$V_{GS} = 0 V \text{ to } 10 V$	-		4.2	6	nC
1010	al Gate Charge	$V_{GS} = 0 V \text{ to } 5 V$			2.4	4	nC
9-	al Gate Charge	_	I <sub>D</sub> = 2.3 A		1.0		nC
Q <sub>gd</sub> Gat	e to Drain "Miller" Charge				1.0		nC
Drain-Source	Diode Characteristics						
V <sub>SD</sub> Sou	rce to Drain Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = 2.3 J$	A (Note 2)		0.8	1.3	V
11	verse Recovery Time	— I <sub>F</sub> = 2.3 A, di/dt = 100 A/μs —			45	73	ns
Q <sub>rr</sub> Rev	verse Recovery Charge				33	53	nC

3. Starting  $T_J$  = 25 °C, L = 1.0 mH,  $I_{AS}$  = 5.0 A,  $V_{DD}$  = 135 V,  $V_{GS}$  = 10 V.

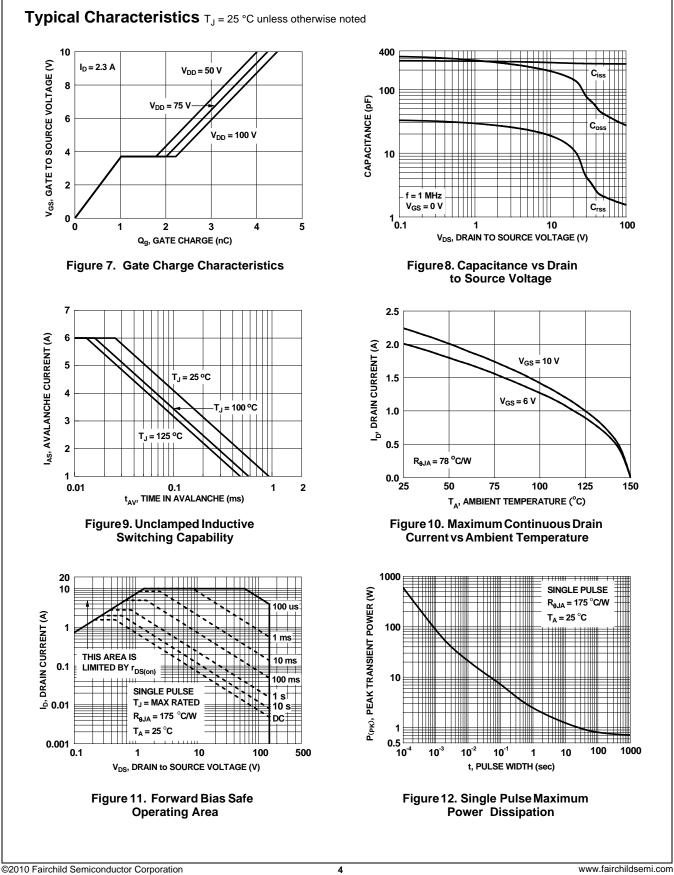
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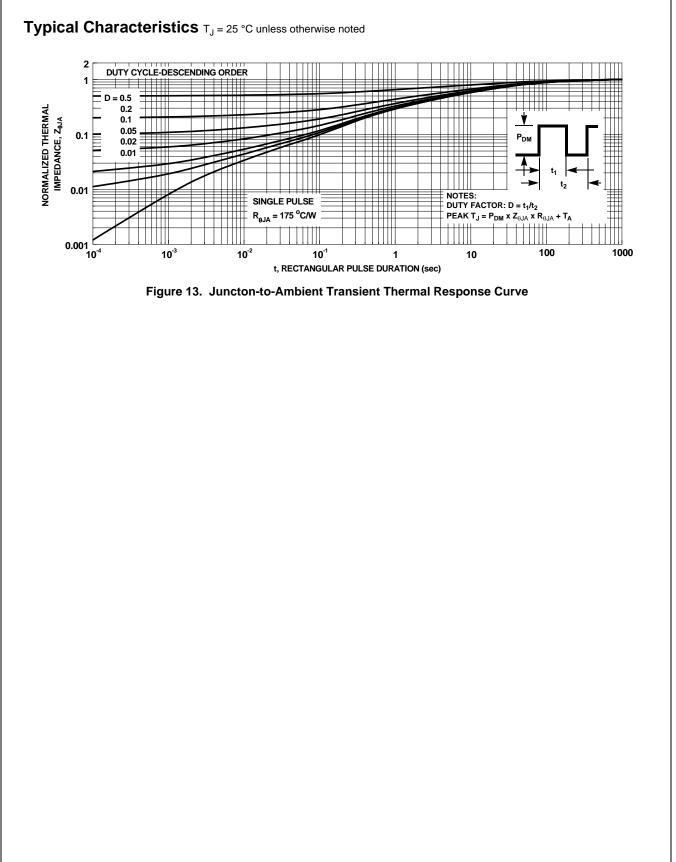
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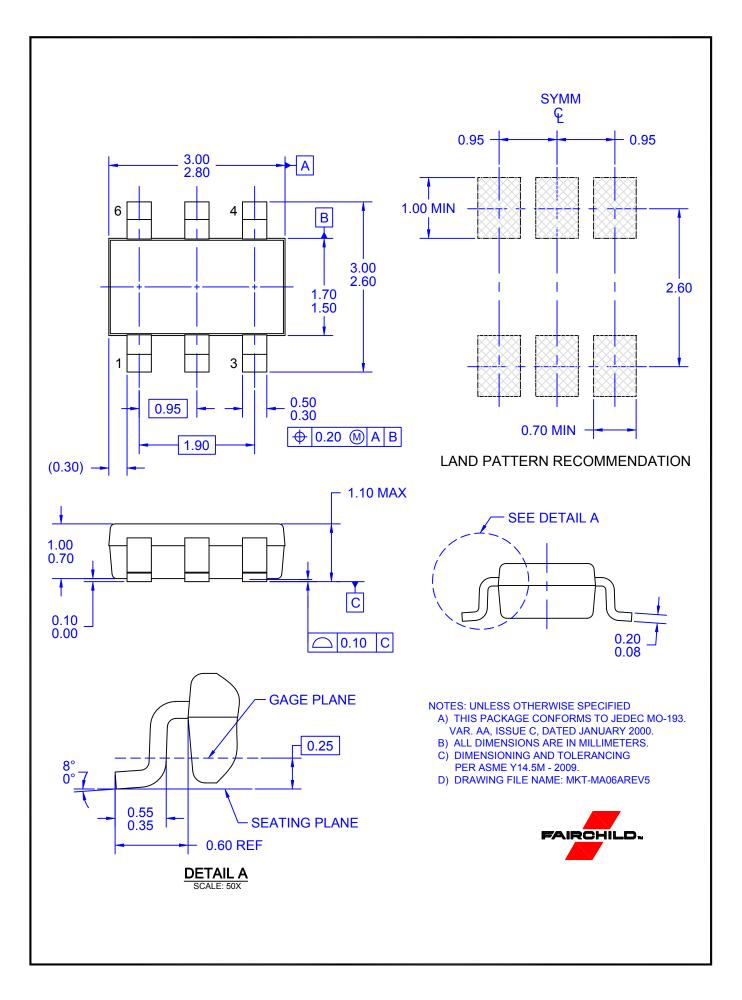


FDC86244 N-Channel Shielded Gate Power Trench<sup>®</sup> MOSFET

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